NPN Medium Power Transistor







Pin Configuration

- 1. Emitter
- 2. Base
- 3. Collector

Features:

- · NPN Silicon Power Switching Transistors.
- · Medium Power Amplifier and Switching Applications

Absolute Maximum Ratings:

 $(T_a = 25^{\circ}C \text{ unless otherwise specified})$

Characteristic	Symbol	BC140-16	BC141-16	Unit
Collector Emitter Voltage	V _{CBO}	40	60	
Collector Base Voltage	V _{CES}	80	100	V
Emitter Base Voltage	V_{EBO}	7		
Collector Current Continuous	I _c	,	1	Α
Power Dissipation at T _a = 25°C Derate above 25°C	D	0. 4.		W
Power Dissipation at T _C = 25°C Derate above 25°C	P _D	4 22.73		mW/°C
Operating Storage Temperature Range	T_{j}, T_{stg}	-65 to	+200	°C

Thermal Resistance

Junction to Ambient in Free Air	R _{th(j-a)}	219	°CAM
Junction to Case	R _{th(j-c)}	44	°C/W

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Electrical Characteristics:

 $(T_a = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
O-lla star Freitter Valta va	V _{CES}	$I_C = 100\mu A, V_{BE} = 0$ BC140-16 BC141-16	80 100			
Collector Emitter Voltage	*V _{CEO}	I _C = 30mA, I _B = 0 BC140-16 40 BC141-16 60			-	V
Emitter Base Voltage	V _{EBO}	$I_{E} = 100 \mu A, I_{C} = 0$	7		-	
Collector Cut off Current	I _{CES}	$V_{CE} = 60V, V_{BE} = 0$		-	100	nA
		$V_{CE} = 60V, V_{BE} = 0, T_a = 150^{\circ}C$] -		100	μA
	*h _{FE}	I _C = 100mA, V _{CE} = 1V BC140-16/BC141-16 Group-6 Group-10 Group-16	40 40 63 100		400 100 160 250	
DC Current Gain		I _C = 1A, V _{CE} = 1V BC140-16/BC141-16 Group-6 Group-10 Group-16	-	26 15 20 30	-	-
Collector Emitter Saturation Voltage	*V _{CE(sat)}	I _C = 1A, I _B = 0.1A			1	\/
Base Emitter on Voltage	*V _{BE(on)}	I _C = 1A, V _{CE} = 1V		-	2	V

Dynamic Characteristics

Transition Frequency	f_{T}	I _C = 50mA, V _{CE} = 10V, f = 20MHz	50		-	MHz
Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz		-	25	د
Input Capacitance	C _{ib}	V _{EB} = 0.5V, I _C = 0, f = 1MHz	-		80	pF

Switching Characteristics

Turn On Time	t _{on}	I _C = 150mA, I _{B1} = 7.5mA			250	
Turn Off Time	t _{off}	I _C = 150mA, I _{B1} = I _{B2} = 7.5mA	_	-	850	ns

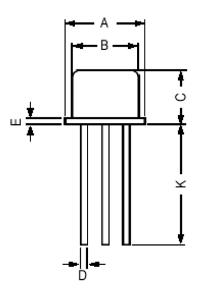
^{*}Pulsed : Pulse Duration ≤300µs, Duty Cycle ≤1%



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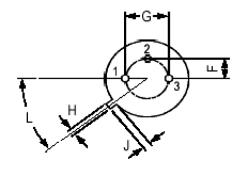


TO-39 Metal Can Package



Dim.	Min.	Max.
Α	8.5	9.39
В	7.74	8.5
С	6.09	6.6
D	0.4	0.53
Е	-	0.88
F	2.41	2.66
G	4.82	5.33
Н	0.71	0.86
J	0.73	1.02
K	12.7	-
L	42°	48°

Dimensions: Millimetres



Pin Configuration

- 1. Emitter
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Part Number Table

Description	Part Number			
Transistor, NPN, TO-39	BC140-16			
	BC141-16			

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